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FIG. 1

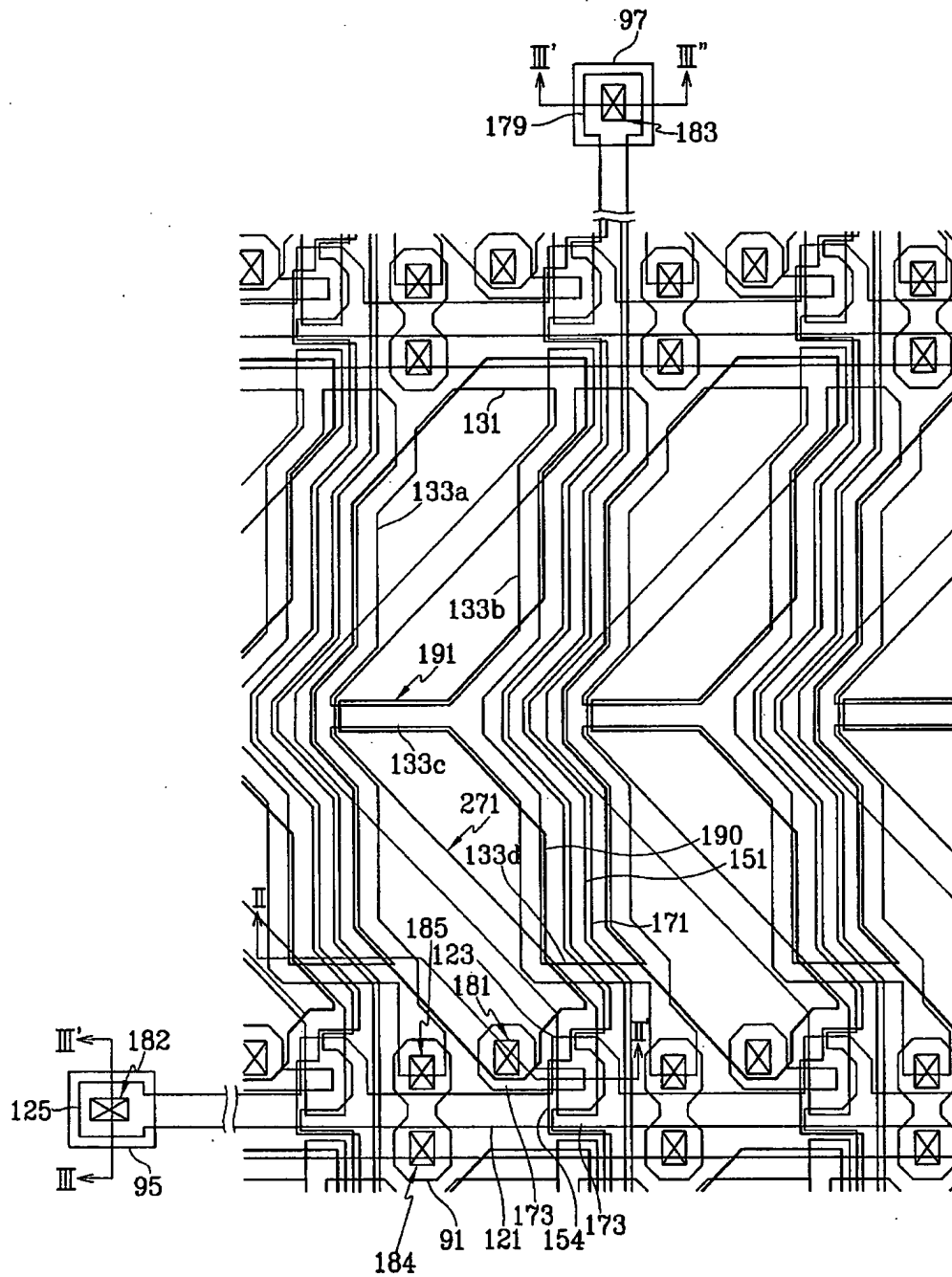


FIG.2

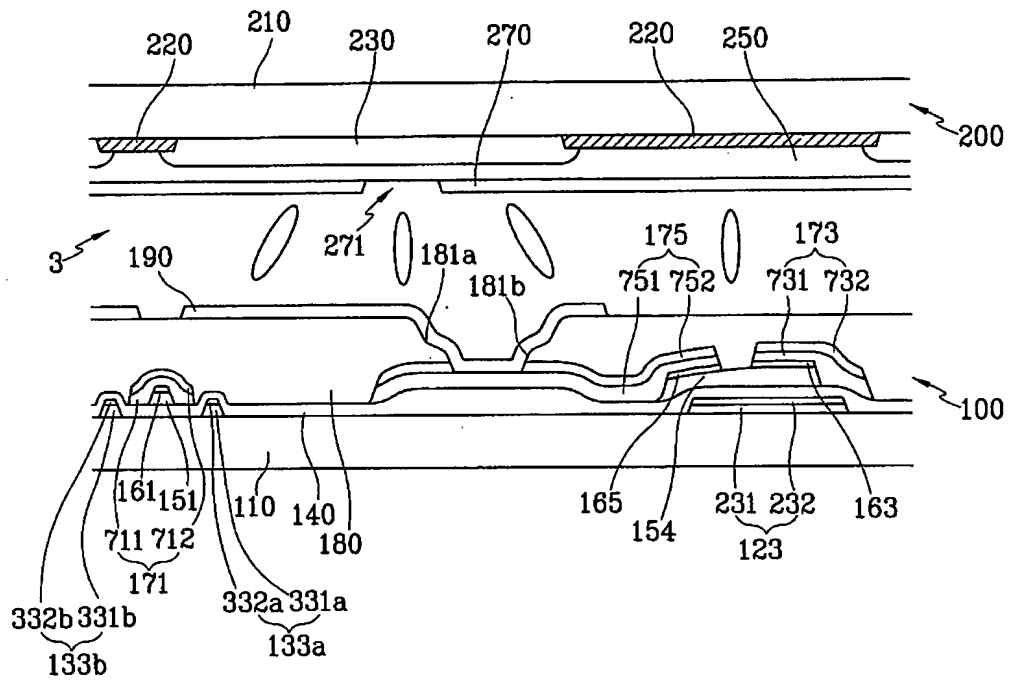


FIG.3

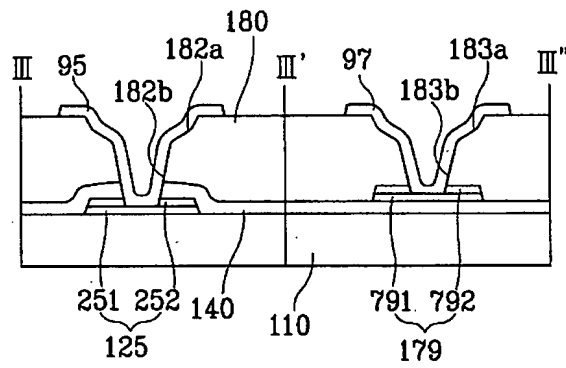


FIG.4A

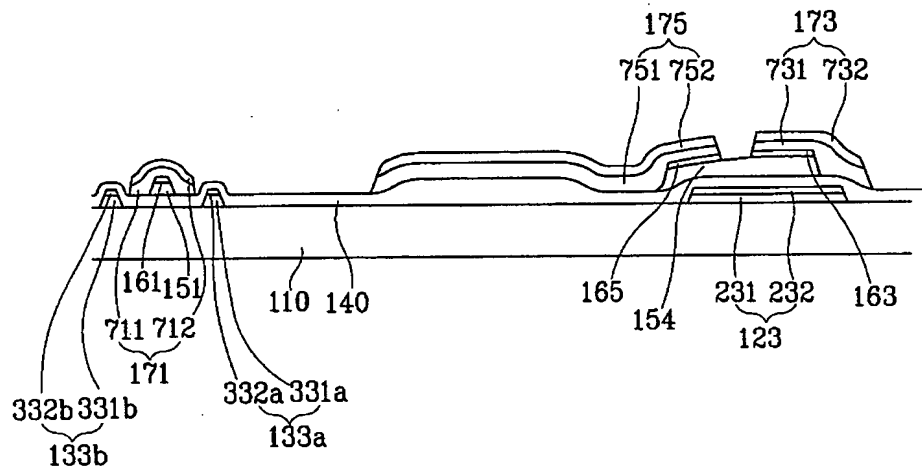


FIG.4B

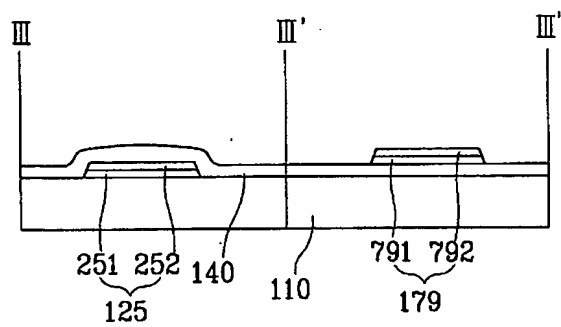


FIG.5A

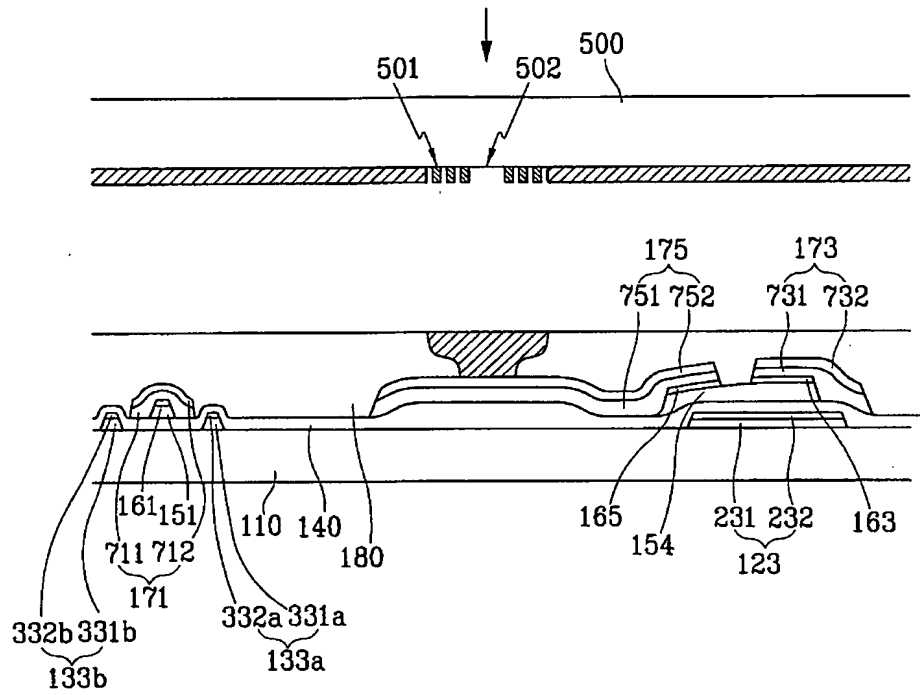


FIG.5B

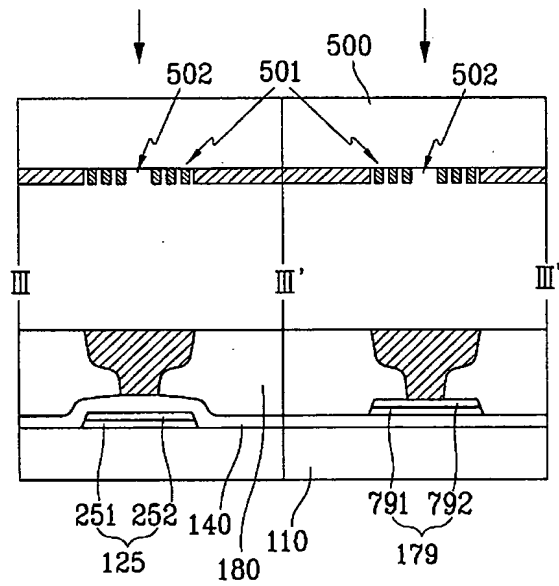


FIG.6

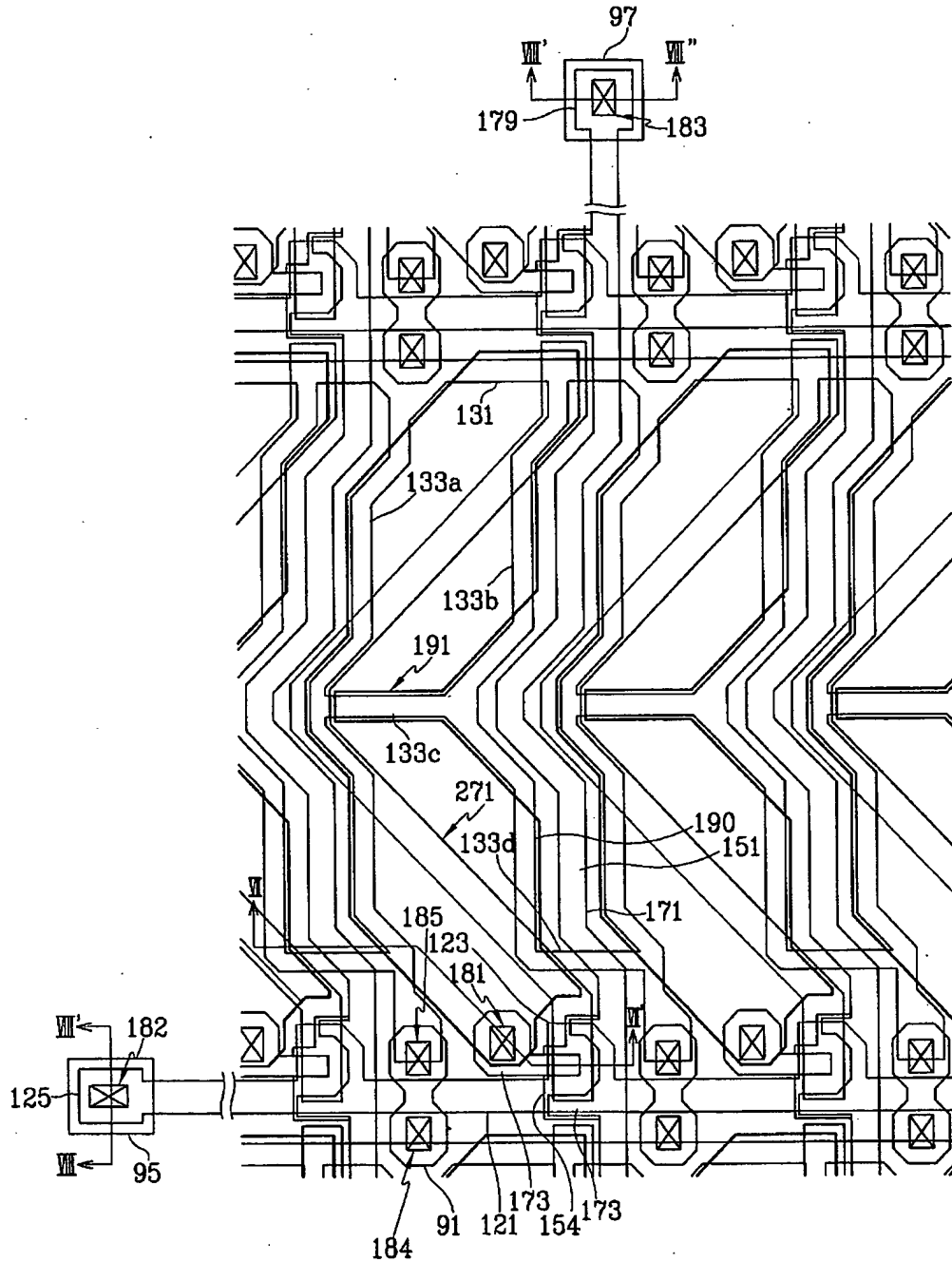


FIG.7

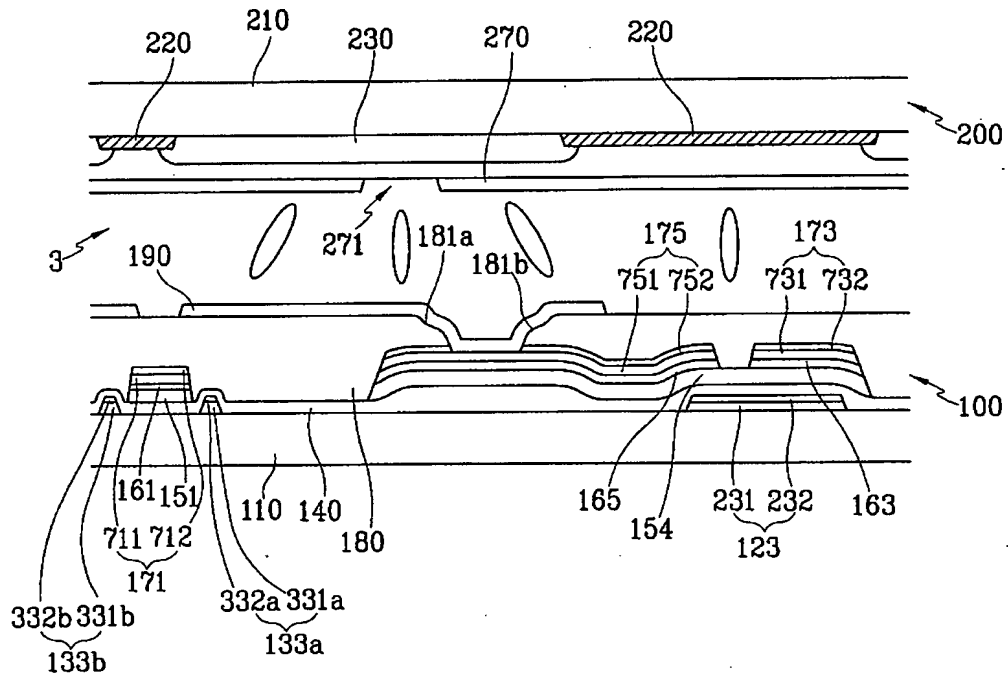


FIG.8

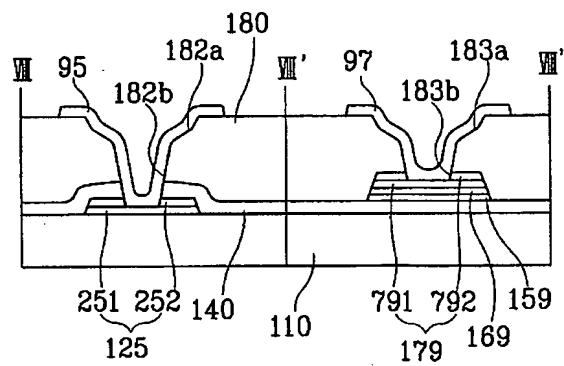


FIG.9A

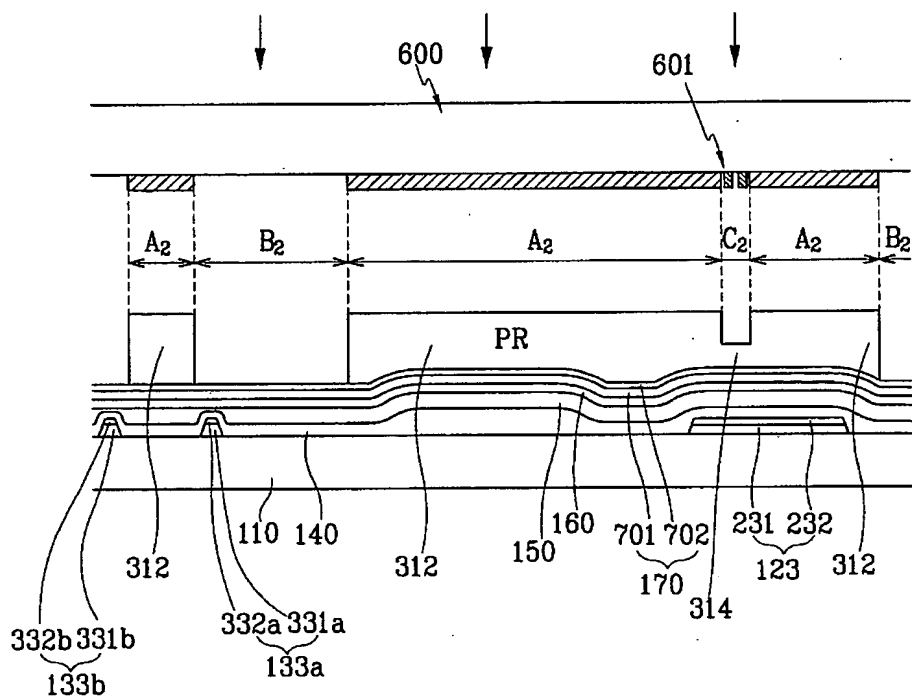


FIG.9B

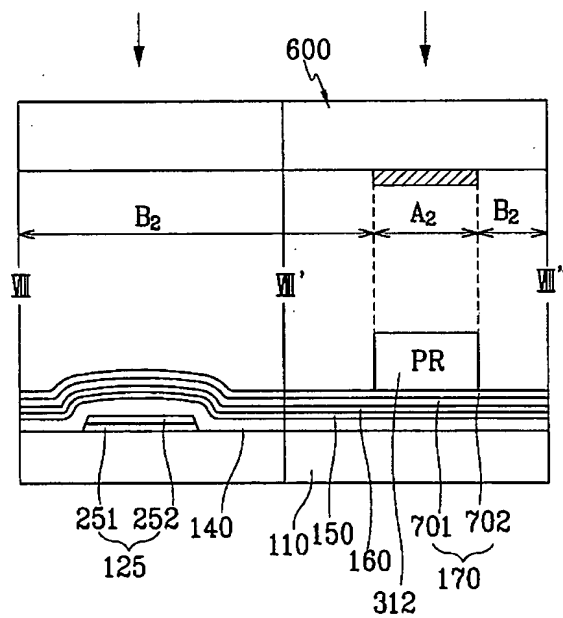


FIG.10A

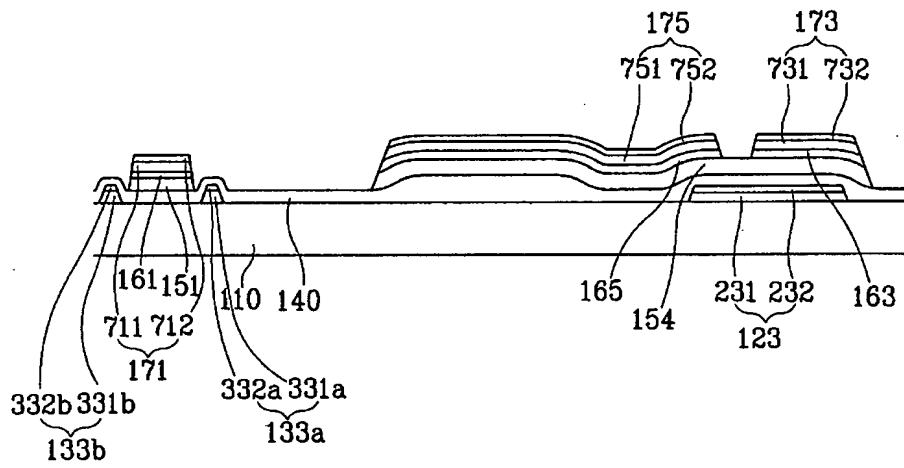


FIG.10B

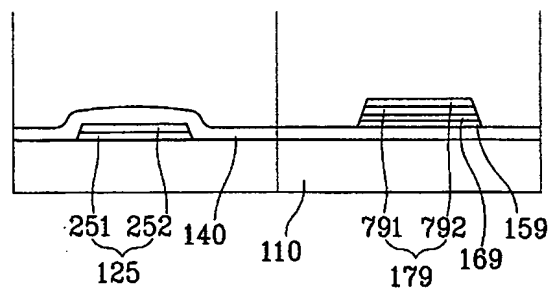


FIG.12

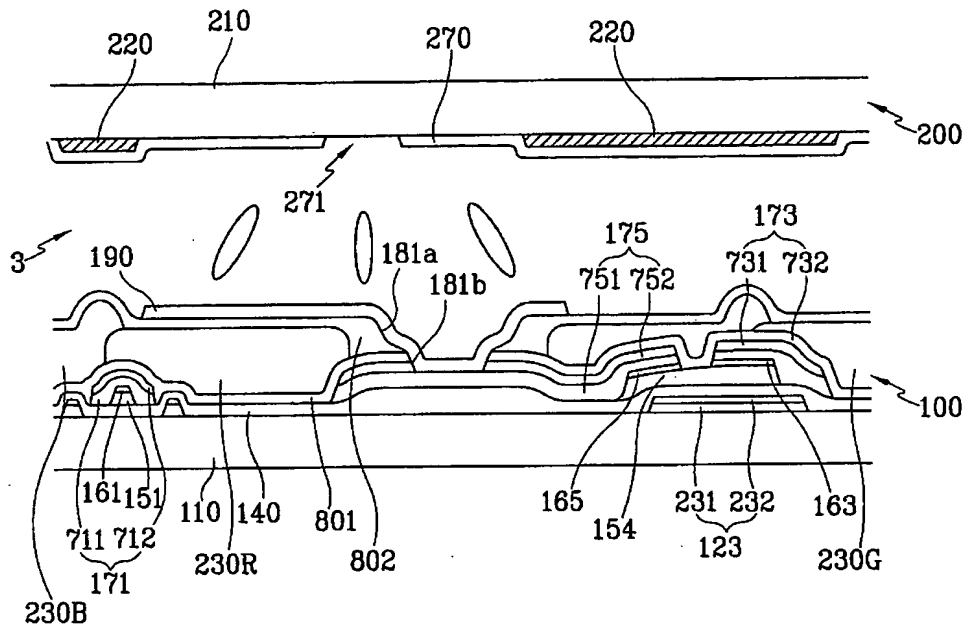
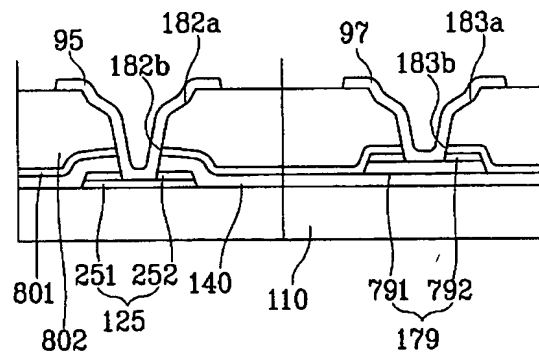


FIG.13



[illegible]

This cross-sectional view shows a semiconductor device with two distinct contact regions. On the left, a contact structure (95) is formed over a substrate (110) with layers 801, 802, 251, and 252. It features a central opening (182b) and side openings (182a). A layer 140 is present beneath the contact. On the right, another contact structure (97) is shown, featuring a central opening (183b) and side openings (183a). This structure is built on layers 791, 792, and 159, with a layer 169 at the base. A common layer 125 is located beneath the first contact, and a layer 179 is beneath the second. A central layer 110 runs through the middle of the device.

FIG.16

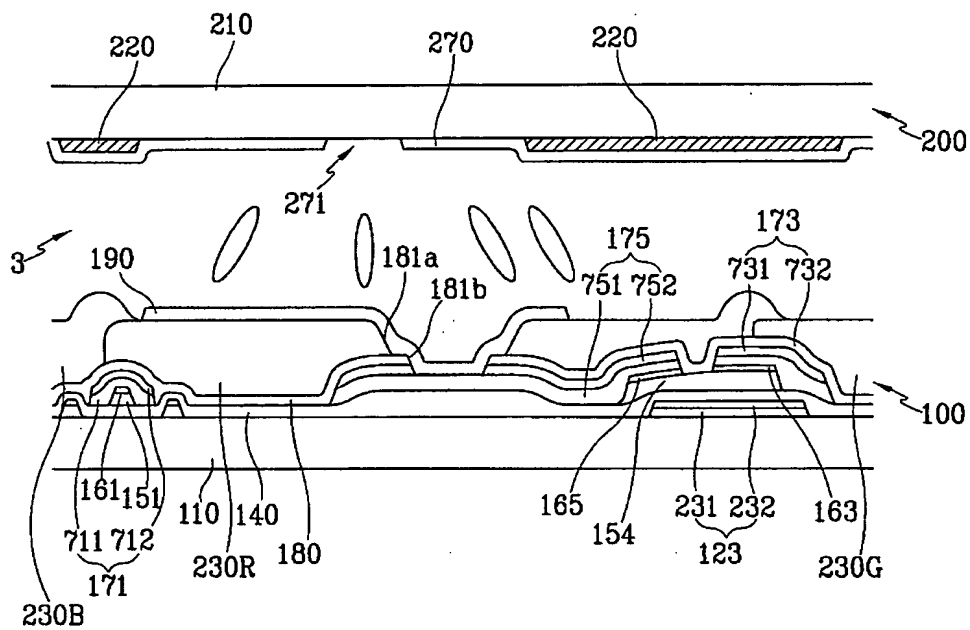
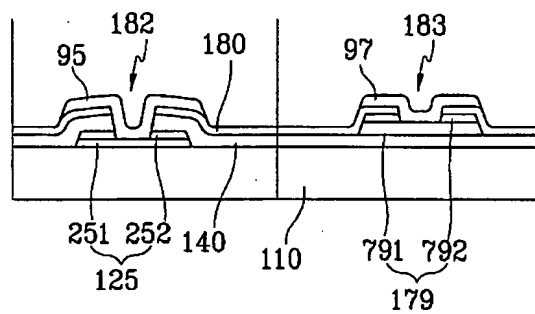


FIG.17



[illegible]